

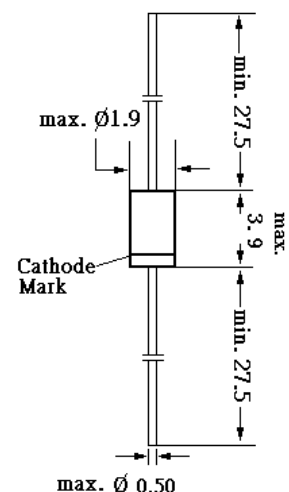
BA243A, BA244A

SILICON EPITAXIAL PLANAR DIODE SWITCHES

for electronic band-switching in radio and TV tuners in the frequency range of 50 to 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped.

Details see "Taping".



Glass case JEDEC DO-35

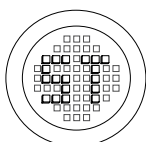
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current at $T_{amb} = 25^\circ\text{C}$	I_F	100	mA
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^\circ\text{C}$

Characteristics at $T_{amb} = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{mA}$	V_F	-	-	1	V
Leakage Current at $V_R = 20\text{V}$	I_R	-	-	50	nA
at $V_R = 15\text{V}, T_{amb} = 60^\circ\text{C}$	I_R	-	-	1	μA
Dynamic Forward Resistance at $f = 50$ to 1000 MHz, $I_F = 10\text{mA}$	r_f	-	0.7	1	Ω
BA243A	r_f	-	0.4	0.5	Ω
BA244A	r_f	-	0.4	0.5	Ω
Relative Variation of Dynamic Forward Resistance with the Variation of Forward Current in the Range of $I_F = 2$ to 40mA	$\frac{\Delta r_f \cdot 100}{r_f \cdot \Delta I_F}$	-	5	-	%/mA
Capacitance at $V_R = 3\text{V}, f = 1\text{MHz}$	C_{tot}	-	-	1.8	pF
Relative Variation of Capacitance with the Variation of Reverse Voltage in the Range of $V_R = 7$ to 20 V, $f = 100\text{MHz}$	$\frac{\Delta C_{tot} \cdot 100}{C_{tot} \cdot \Delta V_R}$	-	1	-	%/V
Series Inductance across Case	L_S	-	2.5	-	nH

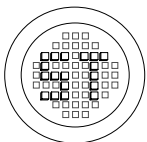
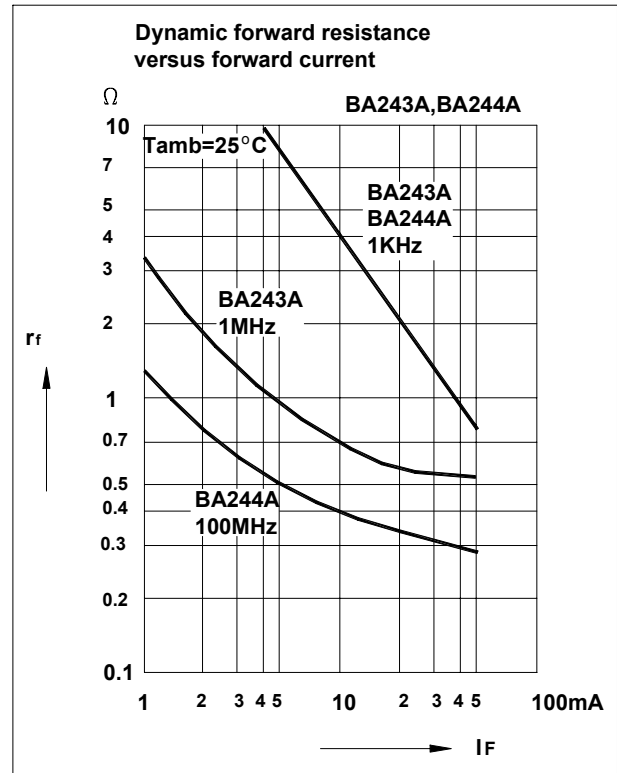
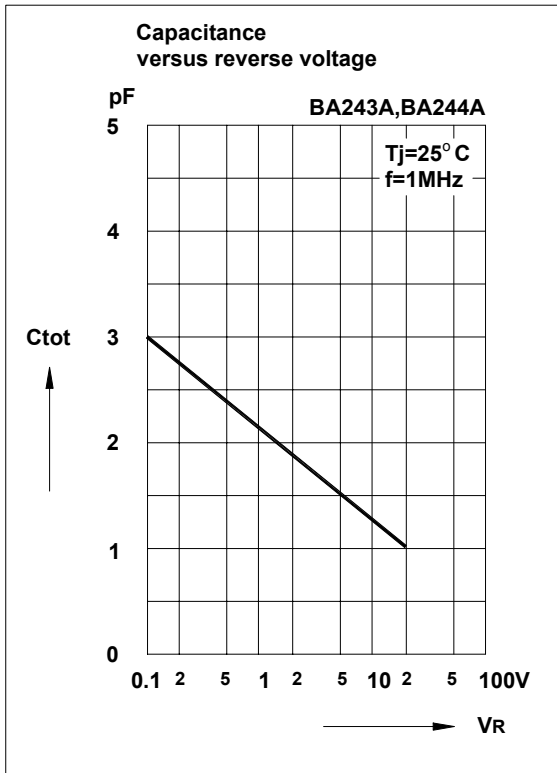


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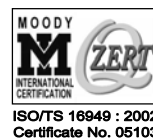
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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 31/12/2002